Solid State Sciences 34 (2014) 63-68

Contents lists available at ScienceDirect

Solid State Sciences

journal homepage: www.elsevier.com/locate/ssscie

Crystal structures and magnetism of $DyAl_xGa_{3-x}$ (where x = 0.33 and x = 0.85)

Pavlo Lyutyy ^{a, c, *}, Oliver Niehaus ^b, Volodymyr Svitlyk ^{b, d}, Rainer Pöttgen ^b, Iryna Porodko ^e, Anatolii Fedorchuk ^f

^a G.V. Karpenko Physico-Mechanical Institute of the NAS of Ukraine, Naukova Street 5, UA-79601 Lviv, Ukraine

^b Institut für Anorganische und Analytische Chemie, Universität Münster, Corrensstrasse 30, Münster D-48149, Germany

^c Institute of Physics, J. Dlugosz University Częstochowa, Armii Krajowej 13/15, Częstochowa, Poland

^d ID27 High Pressure Beamline, ESRF, BP220, 38043 Grenoble, France

^e Lviv Academy of Commerce, Samchuka Str., 9, UA-79011 Lviv, Ukraine

^f S.Z. Gzhytskyj Lviv National University of Veterinary Medicine and Biotechnologies, Pekarska Street 50, UA-79010 Lviv, Ukraine

ARTICLE INFO

Article history: Received 17 January 2014 Received in revised form 28 April 2014 Accepted 17 May 2014 Available online 2 June 2014

Keywords: Ternary compound Gallium Dysprosium Aluminium Crystal structure

ABSTRACT

New ternary compounds have been obtained from arc-melting of the elements. The crystal structures have been investigated by powder X-ray diffraction analysis. $DyAl_{0.33}Ga_{2.67}$ crystallizes in space group $P6_3/mmc$ (a = 6.1649(1) Å, c = 23.0792(1) Å) with $Ta(Rh_{0.33}Pd_{0.67})_3$ -type structure. The structure of $DyAl_{0.85}Ga_{2.15}$ has been refined with rhombohedral symmetry (space group R-3m, a = 6.1702(1) Å, c = 20.7797(1) Å), BaPb₃-type structure. The structures of the compounds have been analyzed crystallographically and the structural relationship has been established. Heat capacity measurements prove antiferromagnetic ordering at Néel temperatures of 12.6(1) K for $DyAl_{0.33}Ga_{2.67}$ and 10.0(1) K for $DyAl_{0.85}Ga_{2.15}$.

© 2014 Elsevier Masson SAS. All rights reserved.

1. Introduction

Rare-earth based compounds are an interesting subject of research due to their widespread potential applications such as permanent magnets [1], magnetocaloric systems [2], hydrogen storage materials [3] and other applications.

A literature review of binary rare-earth-metal systems attracted our attention to the Dy–Ga and Al–Dy systems, namely to the binary compounds DyGa₃ and DyAl₃ which crystallize in numerous polymorphic modifications with closely related structures. According to the Massalski compilation of binary phase diagrams [4], DyGa₃ undergoes two temperature-induced polymorphic modifications. The ht2-DyGa₃ phase crystallize in the AuCu₃ structure type (1045 °C–550 °C), the ht1-DyGa₃ modification adopts the Ta(Rh_{0.33}Pd_{0.67})₃ structure type (550 °C–350 °C) and the rt-DyGa₃

http://dx.doi.org/10.1016/j.solidstatesciences.2014.05.004 1293-2558/© 2014 Elsevier Masson SAS. All rights reserved. phase crystallizes in the Mg₃In structure type (below 350 °C). Dysprosium trialuminide is characterized by the existence of two modifications: the TiNi₃-type one which is stable up to 1005 °C, and a HoAl₃-type (1005–1090 °C) one [4]. A high pressure AuCu₃-type modification is also formed [5]. Metastable PuGa₃ and BaPb₃ polymorphs obtained by rapid solidification, were reported in Ref. [6].

Shifting of phase transition temperatures and/or the stabilization of metastable phases with corresponding changes in physical properties is interesting both from theoretical and practical points of view. Such possibilities were demonstrated in Refs. [7–9] and a significant influence on the magnetic properties was achieved by substitution of a small amount of a nonmagnetic element.

Based on previous results and a literature review, a hypothesis that an isoelectronic Al/Ga atoms replacement ($r(Al)_{at.} = 1.431$, $r(Al)_{at.} = 1.221$, difference in atomic radii ~15% [10]) may have a stabilizing effect was made.

In this work we present results of investigations of the pseudobinary system DyGa₃—DyAl₃, including crystallographic peculiarities of new phases and their magnetic susceptibilities.







^{*} Corresponding author. G.V. Karpenko Physico-Mechanical Institute of the NAS of Ukraine, Naukova Street 5, UA-79601 Lviv, Ukraine. Tel./fax: +380 322 633 088. *E-mail address:* pavlo_lyutyy@ukr.net (P. Lyutyy).

2. Experimental details

2.1. Synthesis and structural analysis

For the investigation of the pseudo-binary system DyGa₃-DyAl₃ nine samples were prepared from elemental Dv (99.95%). Al (99.999%) and Ga (99.99%). During the arc-melting procedure. titanium was heated prior to the melting of the reactant mixtures to further purify the argon atmosphere. The buttons were flipped over several times and remelted to achieve high homogeneity, then weighed back in order to check for possible mass losses. No significant mass loss (more than 1%) was found. The samples were then wrapped in Ta foil, sealed in evacuated fused silica capsules, and annealed at 870 K for 10 days and subsequently quenched in water. The crystal structures of the ternary compounds were refined by the Rietveld method using X-ray powder diffraction data collected on a Guinier Huber G 670 (CuKa₁ radiation) machine. All procedures including indexing, refinement of the profile and structural parameters as well as calculations of interatomic distances were performed with the WINCSD [11] program package.

2.2. Magnetic measurements

Magnetic and heat capacity investigations have been performed for the two samples $Dy_{25}Al_{10}Ga_{65}$ (Ta(Rh_{0.33}Pd_{0.67}-type structure)) and $Dy_{25}Al_{20}Ga_{55}$ (BaPb₃-type structure). The measurements were carried out on a Quantum Design Physical Property Measurement System using the Vibrating Sample Magnetometer and the Heat Capacity option, respectively. For the magnetic (heat capacity) measurements 15.033 (4.278) mg of $Dy_{25}Al_{10}Ga_{65}$ and 17.061 (7.987) mg of $Dy_{25}Al_{20}Ga_{55}$ were used. These small pieces obtained from bulk materials were attached to the sample holder rod by kapton foil. For the heat capacity measurements, the pieces were fixed to a pre-calibrated heat capacity puck using Apiezon N grease. Magnetic investigations were performed in the temperature range of 2.5–300 K with a magnetic flux density up to 80 kOe and heat capacity measurements in the range of 2–300 K.

3. Results and discussion

3.1. Structure determination and refinement

After the substitution of 5 atomic per cent of aluminium by gallium atoms in DyAl₃, the diffraction pattern showed the presence of the DyAl₃ phase (TiNi₃-type) together with a new secondary phase. During further substitution (10%) no TiNi₃-type phase was observed.

After powder data indexing of the Dy25Al65Ga10 sample, the BaPb₃ structure type was taken as an initial model, no additional un-indexed peaks could be observed. The phase with this type remains stable up to 55 at. % Ga. Since aluminium and gallium are p^{1} -elements and they have related chemical nature, Ga/Al (X) statistical mixtures were set in the initial model and the structure was successfully refined. The main crystallographic data were standardized by the STRUCTURE TIDY program [12] and the results of the Rietveld refinement of the Dy₂₅Al₂₀Ga₅₅ (DyAl_{0.8}Ga_{2.2}) sample are summarized in Tables 1, 2 and 4. Graphical representation is shown on Fig. 1a. Other tested derivative models did not yield a successful refinement. No significant changes of the unit cell volumes in the solid solution (BaPb₃-type) were observed, lattice parameters are represented in Table 5. Therefore the packing efficiencies (p.e.) (p.e. = (volume of atoms/volume of unit cell) \times 100%) for the extreme solid solution composition were calculated. It was found that the p.e. for the Dy₂₅Al₁₀Ga₆₅ phase is

Table 1

Structural data and crystallographic data recording/refinement conditions for $DyAl_{0.33(2)}Ga_{2.67(2)}$ and $DyAl_{0.85(2)}Ga_{2.15(2)}.$

Refinement composition	$DyAl_{0.32(2)}Ga_{2.68(2)}$	$DyAl_{0.85(2)}Ga_{2.15(2)}\\$
Structure type	Ta(Rh _{0.33} Pd _{0.67}) ₃	BaPb ₃
Space group	P6 ₃ /mmc	R-3m
Pearson symbol	hP40	hR36
Cell par.		
a, Å	6.1649(1)	6.1702(1)
<i>c</i> , Å	23.0792(1)	20.7797(1)
Cell volume (Å ³)	759.63(3)	685.13(3)
Ζ	10	9
Calculated density (g/cm ³)	7.82	7.32
X-ray machine	Guinier Huber G 670	
Wavelength	CuKa1	
Two-theta range	5.0-100.79	5.0-100.31
Refinement, program	WINCSD	
U, V, W	0.05199; -0.05882;	0.13887; -0.10022;
	0.03532	0.05159
R _I	0.0782	0.0970
R _P	0.1106	0.1167
R _{wP}	0.9204	0.7903

 $R_l = \sum |I_o - I_c| / \sum |I_o|, R_p = \sum |y_{oi} - y_{ci}| / \sum |y_{oi}|, I_o - obs.$ intensity; $I_c - calc.$ intensity; $y_{oi} - exp.$ intensity point; $y_{ci} - calc.$ intensity point.

77% and 66% for the $Dy_{25}Al_{20}Ga_{55}$ phase which explains the constant unit cell volume during the Ga/Al substitution.

Further substitution causes the next phase transition. According to the X-ray phase analyses, the sample with the nominal composition Dy₂₅Al₁₀Ga₆₅ (DyAl_{0.4}Ga_{2.6}) does not belong to the TiNi₃-, BaPb₃- or AuCu₃-type. Crystal structure of this phase was successfully refined in Ta(Rh_{0.33}Pd_{0.67})₃ type, standardized crystallographic are represented in Tables 1, 3 and 4. Fig. 1b shows the graphical representation of the Rietveld refinement.

By comparison with the literature data we can conclude that the compound $DyAl_{2.6-0.8}Ga_{0.4-2.2}$ can be considered as a metastable pseudo-binary compound stabilized by the Al/Ga substitution, similar to rapid solidification as reported in Ref. [6]. $DyAl_{0.33(2)}Ga_{2.67(2)}$ (Ta(Rh_{0.33}Pd_{0.67})₃-type) can be considered as a stabilization of the ht1-DyGa₃ phase, at a temperature 50 K higher than the temperature of its existence.

Since the valence electron concentration remains the same during the isoelectronic Al/Ga substitution we suppose that the stabilizations are induced by the changes of the internal lattice

Table 2

Atomic coordinates and isotropic displacements parameters of DyAl_{0.33(2)}Ga_{2.67(2)}.

Atom	Site	x/a	y/b	z/c	$B_{\rm iso/eg}^{b}$, Å ²
Dy1	2b	0	0	1/4	0.97(4)
Dy2	4f	1/3	2/3	0.0430(1)	1.12(4)
Dy3	4f	2/3	1/3	0.3504(1)	1.07(4)
X1 ^a	6h	0.5186(2)	0.0372(2)	1/4	1.36(7)
X2 ^a	12k	0.1728(2)	2x	0.1494(1)	1.20(6)
X3 ^a	12k	0.1433(1)	2 <i>x</i>	0.5521(1)	0.95(5)

^a Mixed occupation. X1 = 0.98(1)Ga + 0.02(1)Al; X2 = 0.82(1)Ga + 0.18(1)Al; X3 = 0.92(1)Ga + 0.08(1)Al.

Table 3

Atomic coordinates and isotropic displacements parameters of $DyAl_{0.85(2)}Ga_{2.15(2)}$.

Atom	Site	x/a	y/b	z/c	$B_{\rm iso/eg}^{\rm b}$, Å ²
Dy1	3a	0	0	0	1.50(3)
Dy2	6 <i>c</i>	0	0	0.2166(1)	1.02(2)
X1 ^a	9e	1/2	0	0	1.27(4)
X2 ^a	18h	0.4796(1)	0.5203(1)	0.2237(1)	1.43(3)

^a Mixed occupation. X1 = 0.43(1)Al + 0.57(1)Ga; X2 = 0.21(1)Al + 0.79(1)Ga. ^b $B_{iso/eg} = (8\pi^2/3) \sum_i \sum_j \sum_{ij} a_i a_j a_i a_j.$ Download English Version:

https://daneshyari.com/en/article/1504309

Download Persian Version:

https://daneshyari.com/article/1504309

Daneshyari.com